

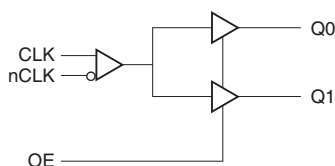
GENERAL DESCRIPTION

The 83026I-01 is a low skew, 1-to-2 Differential-to-LVCMOS/LVTTL Fanout Buffer. The differential input can accept most differential signal types (LVPECL, LVDS, LVHSTL, HCSL and SSTL) and translate to two single-ended LVCMOS/LVTTL outputs. The small 8-lead SOIC footprint makes this device ideal for use in applications with limited board space.

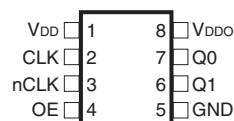
FEATURES

- Two LVCMOS / LVTTL outputs
- Differential CLK, nCLK input pair
- CLK, nCLK pair can accept the following differential input levels: LVPECL, LVDS, LVHSTL, HCSL, SSTL
- Maximum output frequency: 350MHz
- Output skew: 15ps (maximum)
- Part-to-part skew: 600ps (maximum)
- Additive phase jitter, RMS: 0.03ps (typical)
- Small 8 lead SOIC package saves board space
- 3.3V core, 3.3V, 2.5V or 1.8V output operating supply
- -40°C to 85°C ambient operating temperature
- Available in lead-free RoHS (6) package

BLOCK DIAGRAM

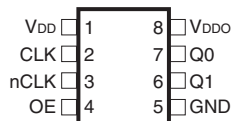


PIN ASSIGNMENT



83026I-01
8-Lead SOIC

3.8mm x 4.8mm, x 1.47mm package body
M Package
Top View



83026I-01
8-Lead TSSOP

4.40mm x 3.0mm x 0.925mm
package body
G Package
Top View

TABLE 1. PIN DESCRIPTIONS

Number	Name	Type	Description
1	V_{DD}	Power	Positive supply pin.
2	CLK	Input	Non-inverting differential clock input.
3	nCLK	Input	Inverting differential clock input. $V_{DD}/2$ default when left floating.
4	OE	Input	Output enable. When HIGH, outputs are enabled. When LOW, outputs are in High Impedance State. LVCMOS / LVTTTL interface levels.
5	GND	Power	Power supply ground.
6	Q1	Output	Clock output. LVCMOS / LVTTTL interface levels.
7	Q0	Output	Clock output. LVCMOS / LVTTTL interface levels.
8	V_{DDO}	Power	Output supply pin.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance			4		pF
C_{PD}	Power Dissipation Capacitance (per output)	$V_{DD}, V_{DDO} = 3.465V$			17	pF
		$V_{DD} = 3.465V, V_{DDO} = 2.625V$			16	pF
		$V_{DD} = 3.465V, V_{DDO} = 1.95V$			15	pF
R_{PULLUP}	Input Pullup Resistor			51		k Ω
$R_{PULLDOWN}$	Input Pulldown Resistor			51		k Ω
R_{OUT}	Output Impedance	$V_{DD}, V_{DDO} = 3.3V$		7		Ω
		$V_{DD} = 3.3V, V_{DDO} = 2.5V$		8		Ω
		$V_{DD} = 3.3V, V_{DDO} = 1.8V$		10		Ω

TABLE 3. CONTROL FUNCTION TABLE

Input	Outputs
OE	Q0, Q1
0	HiZ
1	Active

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, V_O	-0.5V to $V_{DDO} + 0.5V$
Package Thermal Impedance, θ_{JA}	
8 Lead SOIC	112.7°C/W (0 lfpm)
8 Lead TSSOP	101.7°C/W (0 lfpm)
Storage Temperature, T_{STG}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.71V$ TO $3.465V$, $T_A = -40^\circ C$ TO $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
V_{DDO}	Output Supply Voltage		3.135	3.3	3.465	V
			2.375	2.5	2.625	V
			1.71	1.8	1.89	V
I_{DD}	Power Supply Current				10	mA
I_{DDO}	Output Supply Current				3	mA

TABLE 3B. LVCMOS / LVTTTL DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.375V$ TO $3.465V$, $T_A = -40^\circ C$ TO $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	OE	2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage	OE	-0.3		0.8	V
I_{IH}	Input High Current	OE	$V_{DD} = V_{IN} = 3.465V$		5	μA
I_{IL}	Input Low Current	OE	$V_{DD} = 3.465V, V_{IN} = 0V$			μA
V_{OH}	Output High Voltage; NOTE 1	$V_{DDO} = 3.135V$	2.6			V
		$V_{DDO} = 2.375V$	1.8			V
V_{OL}	Output Low Voltage; NOTE 1				0.5	V

NOTE 1: Outputs terminated with 50 Ω to $V_{DDO}/2$. See Parameter Measurement Information section, "Output Load Test Circuit" diagrams.

TABLE 3C. LVCMOS / LVTTTL DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 5\%$, $T_A = -40^\circ C$ TO $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	OE	2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage	OE	-0.3		0.8	V
I_{IH}	Input High Current	OE	$V_{DD} = V_{IN} = 3.465V$		5	μA
I_{IL}	Input Low Current	OE	$V_{DD} = 3.465V, V_{IN} = 0V$			μA
V_{OH}	Output High Voltage	$I_{OH} = -100\mu A$	$V_{DDO} - 0.2$			V
		$I_{OH} = -2mA$	$V_{DDO} - 0.45$			V
V_{OL}	Output Low Voltage	$I_{OL} = 100\mu A$			0.2	V
		$I_{OL} = 2mA$			0.45	V

TABLE 3D. DIFFERENTIAL DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.71V$ TO $3.465V$, $T_A = -40^\circ C$ TO $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
I_{IH}	Input High Current	nCLK $V_{IN} = V_{DD} = 3.465V$			150	μA
		CLK $V_{IN} = V_{DD} = 3.465V$			150	μA
I_{IL}	Input Low Current	nCLK $V_{IN} = 0V, V_{DD} = 3.465V$	-150			μA
		CLK $V_{IN} = 0V, V_{DD} = 3.465V$	-5			μA
V_{PP}	Peak-to-Peak Input Voltage; NOTE 1		0.15		1.3	V
V_{CMR}	Common Mode Input Voltage; NOTE 2, 3		GND + 0.5		$V_{DD} - 0.85$	V

NOTE 1: V_{PP} can exceed 1.3V provided that there is sufficient offset level to keep $V_{IL} > 0V$.

NOTE 2: For single ended applications, the maximum input voltage for CLK, nCLK is $V_{DD} + 0.3V$.

NOTE 3: Common mode voltage is defined as V_{IH} .

TABLE 4A. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ TO $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				350	MHz
t_{PD}	Propagation Delay; NOTE 1	$f \leq 350MHz$	1.3	1.9	2.5	ns
$t_{sk(o)}$	Output Skew; NOTE 2, 4				15	ps
$t_{sk(pp)}$	Part-to-Part Skew; NOTE 3, 4				900	ps
t_{jit}	Buffer Additive Phase Jitter, RMS, refer to Additive Phase Jitter Section			0.03		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	150		800	ps
odc	Output Duty Cycle	$f \leq 66MHz$	48		52	%
		$67MHz \leq f \leq 166MHz$	45		55	%
		$167MHz \leq f \leq 350MHz$	40		60	%

NOTE 1: Measured from the differential input crossing point to $V_{DDO}/2$ of the output.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at $V_{DDO}/2$.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{DDO}/2$.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 6.

TABLE 4B. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ TO $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				350	MHz
t_{PD}	Propagation Delay; NOTE 1	$f \leq 350MHz$	1.5	2.0	2.6	ns
$tsk(o)$	Output Skew; NOTE 2, 4				15	ps
$tsk(pp)$	Part-to-Part Skew; NOTE 3, 4				750	ps
t_{jit}	Buffer Additive Phase Jitter, RMS, refer to Additive Phase Jitter Section			0.03		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	150		800	ps
odc	Output Duty Cycle	$f \leq 66MHz$	48		52	%
		$67MHz \leq f \leq 166MHz$	46		54	%
		$167MHz \leq f \leq 350MHz$	40		60	%

NOTE 1: Measured from the differential input crossing point to $V_{DDO}/2$ of the output.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at $V_{DDO}/2$.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{DDO}/2$.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 4C. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 5\%$, $T_A = -40^{\circ}C$ TO $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				350	MHz
t_{PD}	Propagation Delay; NOTE 1	$f \leq 350MHz$	1.9	2.5	3.1	ns
$tsk(o)$	Output Skew; NOTE 2, 4				15	ps
$tsk(pp)$	Part-to-Part Skew; NOTE 3, 4				600	ps
t_{jit}	Buffer Additive Phase Jitter, RMS, refer to Additive Phase Jitter Section			0.03		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	200		900	ps
odc	Output Duty Cycle	$f \leq 66MHz$	48		52	%
		$67MHz \leq f \leq 166MHz$	43		57	%
		$167MHz \leq f \leq 350MHz$	40		60	%

NOTE 1: Measured from the differential input crossing point to $V_{DDO}/2$ of the output.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at $V_{DDO}/2$.

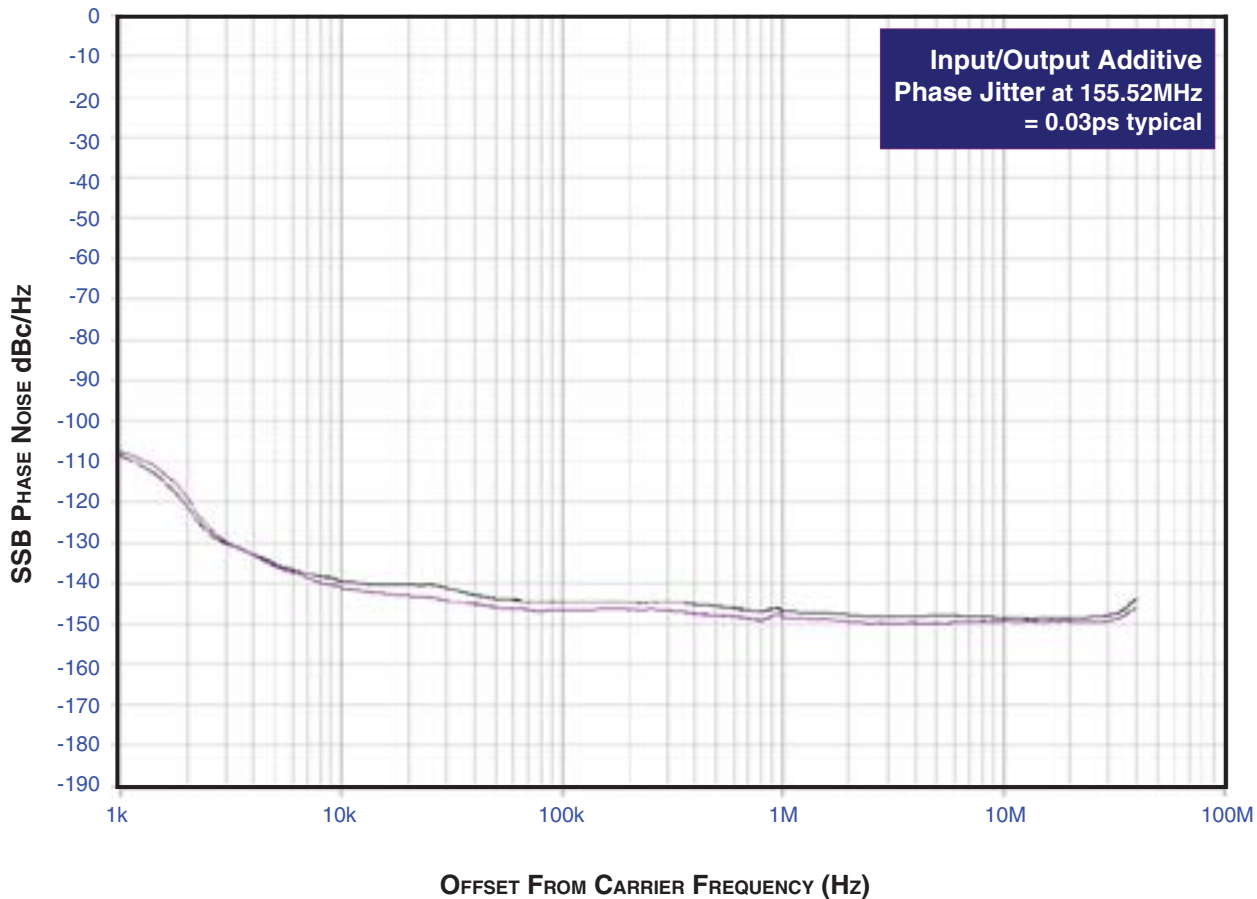
NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{DDO}/2$.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

ADDITIVE PHASE JITTER

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the **dBc Phase Noise**. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the

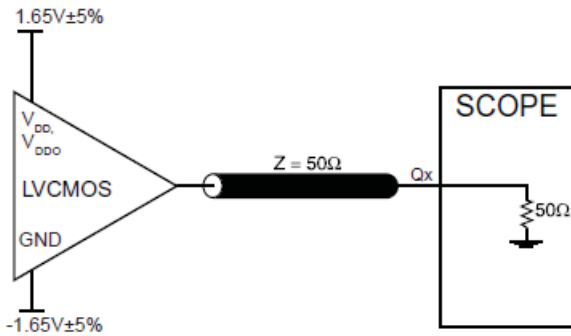
1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a **dBc** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



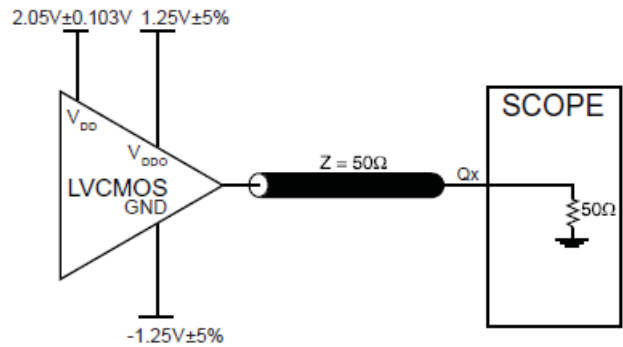
As with most timing specifications, phase noise measurements have issues. The primary issue relates to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The

device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependant on the input source and measurement equipment.

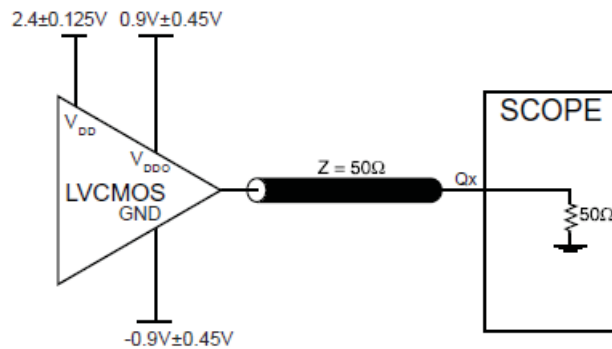
PARAMETER MEASUREMENT INFORMATION



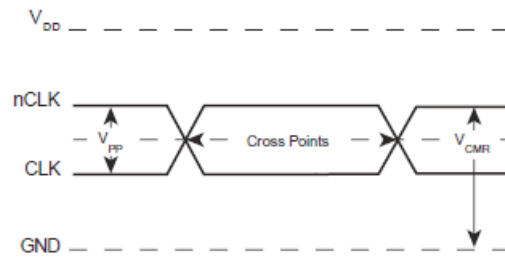
3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT



3.3V CORE/2.5V OUTPUT LOAD AC TEST CIRCUIT



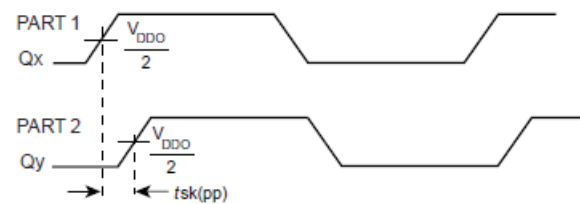
3.3V CORE/1.8V OUTPUT LOAD AC TEST CIRCUIT



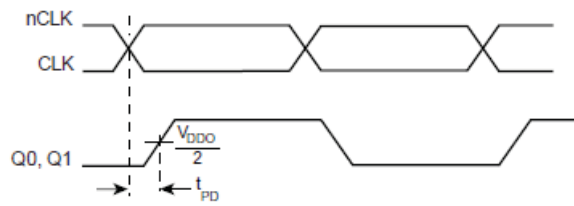
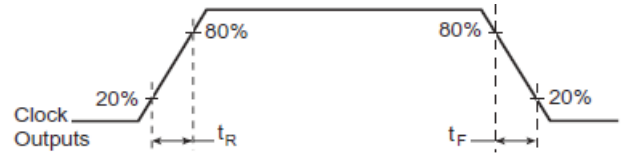
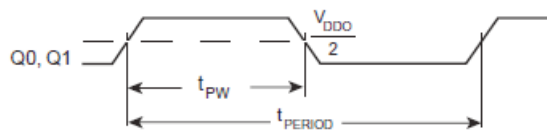
DIFFERENTIAL INPUT LEVEL



OUTPUT SKEW



PART-TO-PART SKEW


PROPAGATION DELAY

OUTPUT RISE/FALL TIME


$$odc = \frac{t_{PW}}{t_{PERIOD}} \times 100\%$$

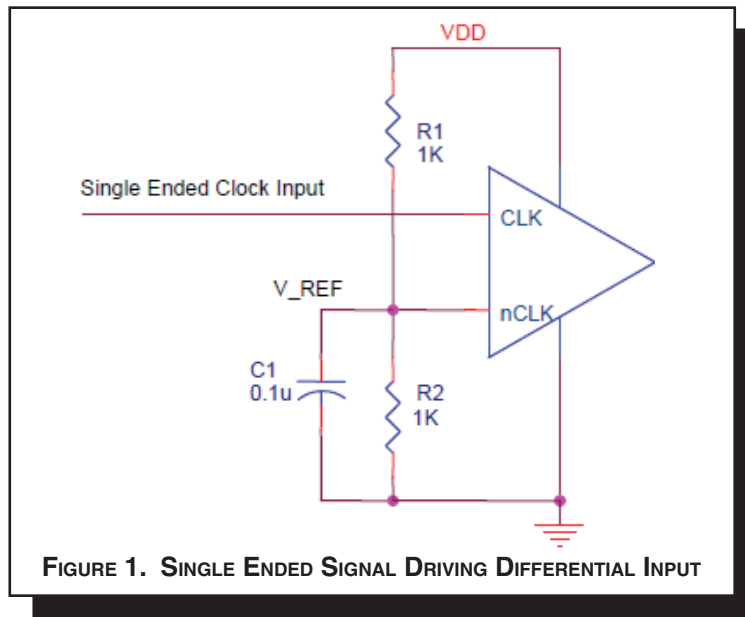
OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD

APPLICATION INFORMATION

WIRING THE DIFFERENTIAL INPUT TO ACCEPT SINGLE ENDED LEVELS

Figure 1 shows how the differential input can be wired to accept single ended levels. The reference voltage $V_{REF} = V_{DD}/2$ is generated by the bias resistors R1, R2 and C1. This bias circuit should be located as close as possible to the input pin. The ratio

of R1 and R2 might need to be adjusted to position the V_{REF} in the center of the input voltage swing. For example, if the input clock swing is only 2.5V and $V_{DD} = 3.3V$, V_{REF} should be 1.25V and $R2/R1 = 0.609$.



RECOMMENDATIONS FOR UNUSED OUTPUT PINS

OUTPUTS:

LVC MOS OUTPUTS

All unused LVC MOS output can be left floating. We recommend that there is no trace attached.

SCHEMATIC EXAMPLE

Figure 3 shows an application schematic example of 83026I-01. The 83026I-01 CLK/nCLK input can directly accept various types of differential signal. In this example, the input is driven by an LVDS driver. The 83026I-01 outputs are LVC MOS drivers. In

this example, series termination approach is shown. Additional termination approaches are shown in the LVC MOS Termination Application Note.

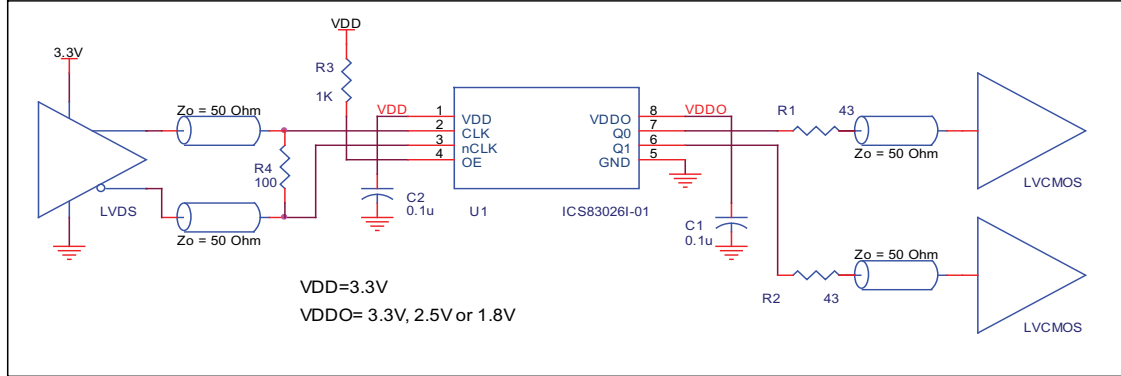


FIGURE 3. 83026I-01 SCHEMATIC EXAMPLE

RELIABILITY INFORMATION

TABLE 5A. θ_{JA} VS. AIR FLOW TABLE FOR 8 LEAD SOIC

θ_{JA} by Velocity (Linear Feet per Minute)			
	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	153.3°C/W	128.5°C/W	115.5°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	112.7°C/W	103.3°C/W	97.1°C/W

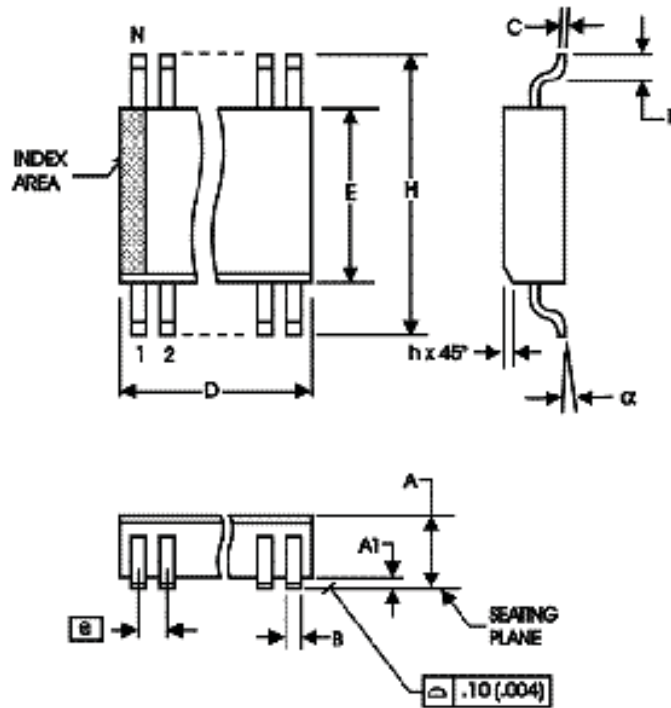
NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

TABLE 5B. θ_{JA} VS. AIR FLOW TABLE FOR 8 LEAD TSSOP

θ_{JA} by Velocity (Linear Feet per Minute)			
	0	200	500
Multi-Layer PCB, JEDEC Standard Test Boards	101.7°C/W	90.5°C/W	89.8°C/W

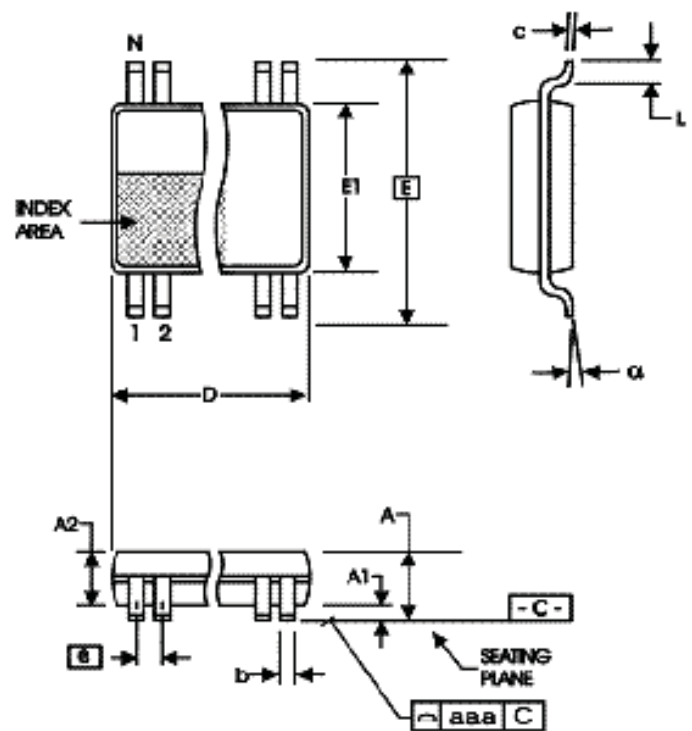
TRANSISTOR COUNT

The transistor count for ICS83026I-01 is: 260

PACKAGE OUTLINE - SUFFIX M FOR 8 LEAD SOIC

TABLE 6A. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	MINIMUM	MAXIMUM
N	8	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BASIC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
α	0°	8°

Reference Document: JEDEC Publication 95, MS-012

PACKAGE OUTLINE - G SUFFIX FOR 8 LEAD TSSOP

TABLE 6B. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	Minimum	Maximum
N	8	
A	--	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	2.90	3.10
E	6.40 BASIC	
E1	4.30	4.50
e	0.65 BASIC	
L	0.45	0.75
α	0°	8°
aaa	--	0.10

Reference Document: JEDEC Publication 95, MO-153

TABLE 7. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
83026BMI-01LF	026BI01L	8 lead "Lead Free" SOIC	Tube	-40°C to +85°C
83026BMI-01LFT	026BI01L	8 lead "Lead Free" SOIC	Tape and Reel	-40°C to +85°C
83026BGI-01LF	BI01L	8 lead "Lead Free" TSSOP	Tube	-40°C to +85°C
83026BGI-01LFT	BI01L	8 lead "Lead Free" TSSOP	Tape and Reel	-40°C to +85°C

REVISION HISTORY SHEET				
Rev	Table	Page	Description of Change	Date
A	T7	1	Added 8 Lead TSSOP package to Pin Assignment.	6/25/04
		3	Absolute Maximum Ratings - added 8 Lead TSSOP to Package Thermal Impedance.	
		11	Added 8 Lead TSSOP Reliability Information table.	
		13	Added 8 Lead TSSOP Package Outline and Package Dimensions. Ordering Information Table - added 8 Lead TSSOP ordering information.	
A		6	Additive Phase Jitter - corrected X axis on plot.	8/2/05
A	T3C	3	LVC MOS DC Characteristics - corrected Test Conditions for IIH and IIL.	8/12/05
A	T7	1	Features Section - added lead-free bullet	1/16/06
		9	Added Recommendations for Unused Output Pins.	
A	T7	13	Ordering Information Table - added lead-free part number, marking, and note.	10/22/07
		13	Ordering Information Table - added lead-free marking	
A	T7	13	Updated datasheet's header/footer with IDT from ICS.	8/4/10
		15	Removed ICS prefix from Part/Order Number column. Added Contact Page.	
A	T7	1	Removed the ICS prefix on part numbers.	12/15/15
		13	Features Section - removed reference to leaded packages. Ordering Information - removed 2500 from Tape and Reel. Removed LF note below the table. Updated datasheet header and footer	



Corporate Headquarters
6024 Silver Creek Valley Road
San Jose, CA 95138 USA
www.IDT.com

Sales
1-800-345-7015 or 408-284-8200
Fax: 408-284-2775
www.IDT.com/go/sales

Tech Support
www.idt.com/go/support

DISCLAIMER Integrated Device Technology, Inc. (IDT) reserves the right to modify the products and/or specifications described herein at any time, without notice, at IDT's sole discretion. Performance specifications and operating parameters of the described products are determined in an independent state and are not guaranteed to perform the same way when installed in customer products. The information contained herein is provided without representation or warranty of any kind, whether express or implied, including, but not limited to, the suitability of IDT's products for any particular purpose, an implied warranty of merchantability, or non-infringement of the intellectual property rights of others. This document is presented only as a guide and does not convey any license under intellectual property rights of IDT or any third parties.

IDT's products are not intended for use in applications involving extreme environmental conditions or in life support systems or similar devices where the failure or malfunction of an IDT product can be reasonably expected to significantly affect the health or safety of users. Anyone using an IDT product in such a manner does so at their own risk, absent an express, written agreement by IDT.

Integrated Device Technology, IDT and the IDT logo are trademarks or registered trademarks of IDT and its subsidiaries in the United States and other countries. Other trademarks used herein are the property of IDT or their respective third party owners.

For datasheet type definitions and a glossary of common terms, visit www.idt.com/go/glossary.

Copyright ©2015 Integrated Device Technology, Inc. All rights reserved.